



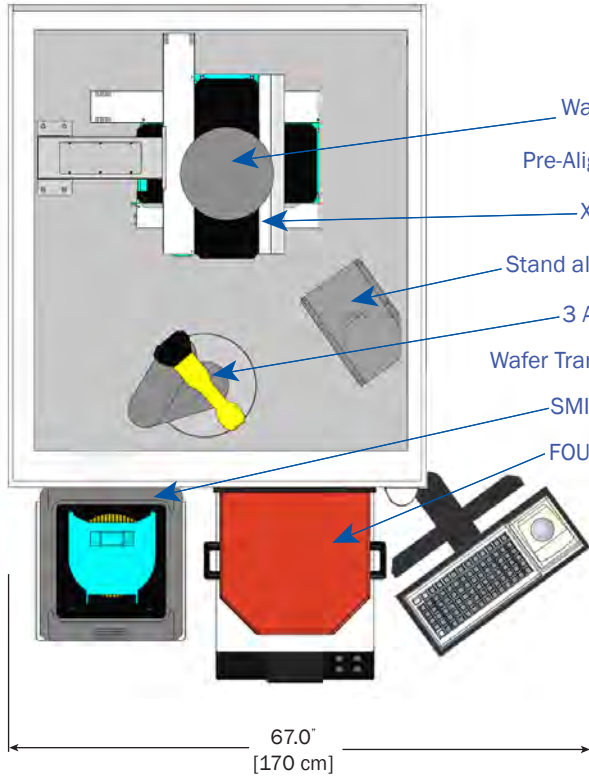
LITTLE FOOT-CD

Ultra-High Resolution &
Ultra-High Sensitivity Scatterometer with
Thin Film Measurement Capabilities and
Reduced Footprint for 200 mm and 150 mm Wafers

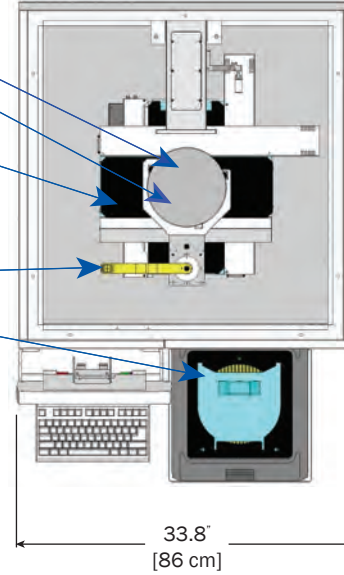
FULLY AUTOMATED, HIGH THROUGHPUT OPTICAL
METROLOGY SYSTEM FOR SEMICONDUCTOR APPLICATIONS.
APPROXIMATELY 40% REDUCTION IN FOOTPRINT COMPARED
TO OTHER METROLOGY TOOLS.

LITTLEFOOT-CD

n&k OptiPrime Series
Conventional Wafer Handling Technology



LittleFoot Series
Revolutionary Wafer Handling Mechanism



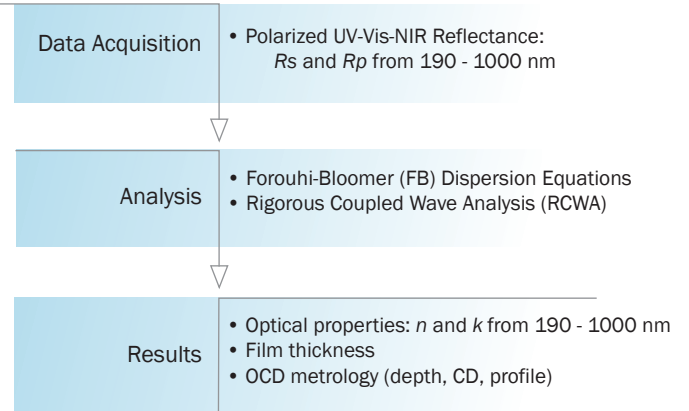
KEY QUALITIES OF LITTLEFOOT-CD

- ~40% Smaller Footprint than Standard Tools Translates into Significant Savings in the Construction and Utilization of Wafer Fabs
- Optimized Polarized Reflectance (R_s and R_p) Data
 - Wavelength Range: 190 - 1000 nm in 1 nm Intervals
 - Micro-Spot Technology
- Identical Analytical Capabilities as the n&k OptiPrime-CD
- Can be Configured for 200 mm (8") and 150 mm (6") Wafers
- Fully Automated
- Based on Patented Reflective Optics that Optimizes the Signal-to-Noise Ratio
- Strong Sensitivity to Sub-Nanometer Material Variations
- Thin Film Measurements:
 - Thickness, n and k (from 190 - 1000 nm)
- OCD Metrology for 2-D and 3-D Structures (Trenches and Contact Holes)
 - Depth, CD, Profile
- Cognex Pattern Recognition Software
- No Re-Alignment Issue Upon Light Bulb Replacement
- Modular design - Easy to Maintain and Service
- GEM/SECS Communication Interface
- SEMI Standard and Third Party Certifications

PHYSICAL CHARACTERISTICS

Dimensions (W x D x H):	86 cm x 121 cm x 180 cm
Weight (unpacked):	300 Kg
Facility Requirements:	100 - 240 VAC, 50/60 Hz, 1 Φ Vacuum

SYSTEM OPERATION FLOW



OPTICAL METROLOGY REQUIREMENTS FULFILLED BY LITTLEFOOT-CD

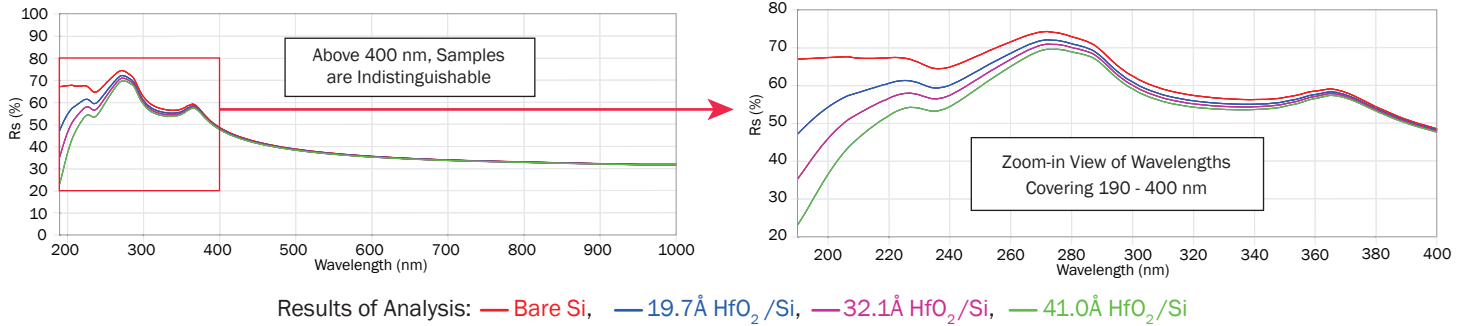
- Optimized Signal-to-Noise Ratio & Large Dynamic Range of Detection
- Wide Wavelength Range (190-1000 nm) & High Resolution
- Physically Valid Model (Forouhi-Bloomer and RCWA)
- User-Friendly, Proprietary Software
- Unlike competitive systems, the n&k LittleFoot-CD has the capability to analyze any new film without sending samples to the factory

Thin Film Application Examples

The n&k LittleFoot-CD's thin film applications cover both current and next generation thin film measurement demands for R&D and production: Ultra Thin Films and Residual Layers, Multi-Layer Stacks, Inhomogeneous Films, 193 nm and 248 nm ARCs and Resists, Low- κ Films, High- κ Films, and films deposited on practically any substrate.

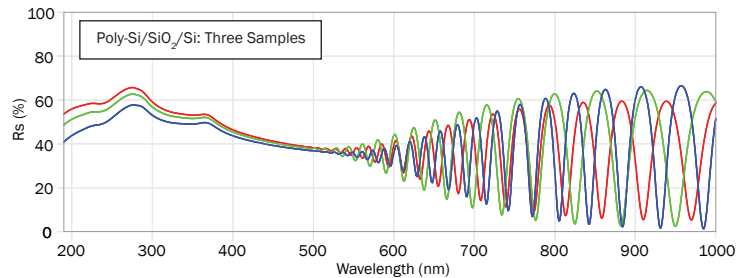
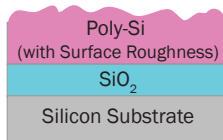
HIGH-K GATE INSULATORS: ATOMIC LAYER DEPOSITION (ALD)

- DUV wavelengths are necessary in order to distinguish the ultra-thin HfO_2 films
- Measurement examples of HfO_2 on a Si-Substrate demonstrates that the tool has plenty of sensitivity in the DUV for this measurement



ROUGH POLY-Si ON SiO_2

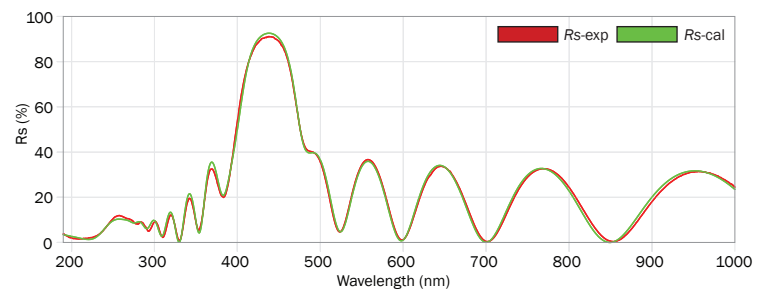
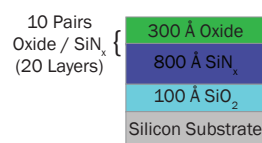
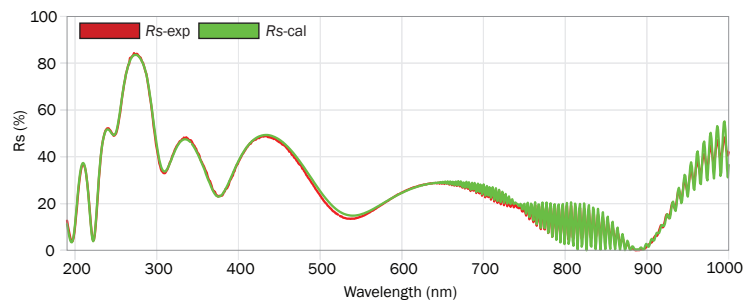
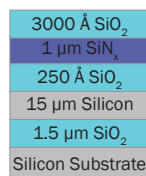
- The wide wavelength range (190 - 1000 nm) of the LittleFoot-CD is needed in order to simultaneously measure the surface roughness and film thickness values
- The data is sensitive to the n and k values of the Poly-Si layer, which can be measured to determine the silicon properties (from amorphous to crystalline)



Spectra	Surface Roughness (Å)	Poly-Si Thickness (Å)	SiO_2 Thickness (Å)
Red	32	18245	505
Green	57	15078	622
Blue	85	21330	765

COMPLEX MULTI-LAYER FILM STRUCTURE

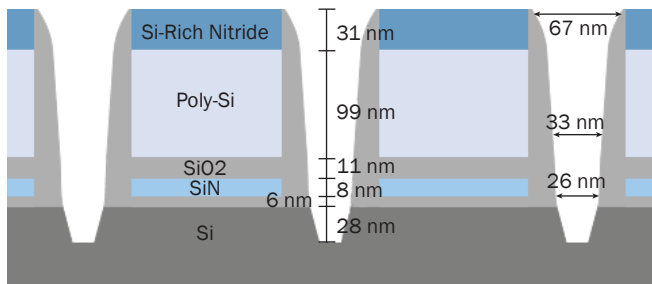
- Complex multilayer film stacks can be measured with the LittleFoot-CD
- Super structures, with sets of repeating layers, can be fully modeled in the analysis software
- Film stacks containing over 80 layers have been successfully measured



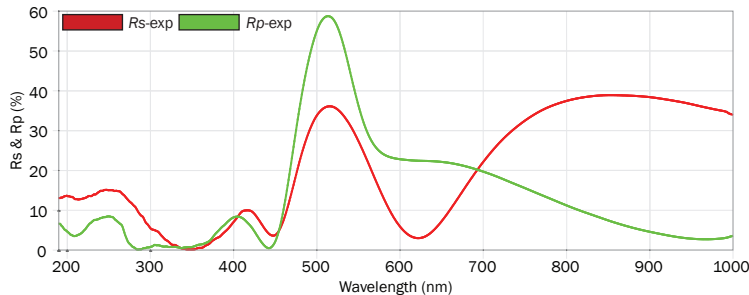
OCD Scatterometry Application Examples

The n&k LittleFoot-CD's OCD scatterometry applications cover structures with very large pitches and very small pitches, 2-D and 3-D complex structures including films inside and outside of shallow and deep trenches and contact holes. Because of our patented and unique optical design, n&k Technology offers the highest signal-to-noise ratio and lowest cost of ownership to support your OCD requirement.

2-D COMPLEX STRUCTURE

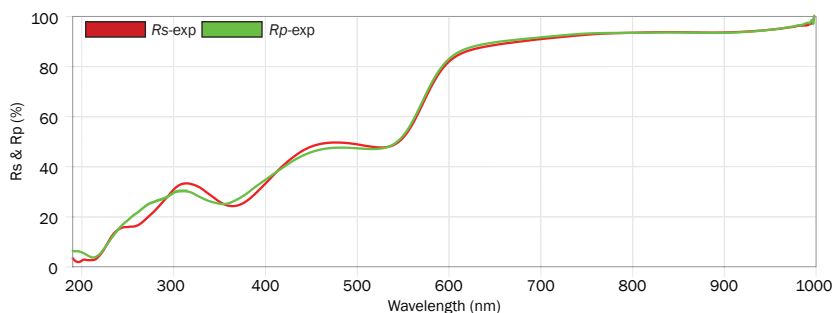
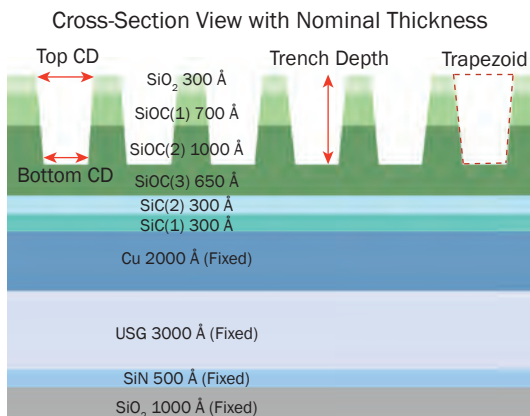


n&k Results - Cross Sectional View



Experimental Spectra Showing Distinct Rs and Rp Polarized Spectra

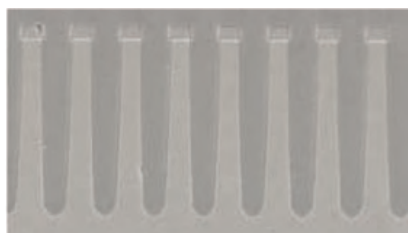
MEASUREMENT OF THIN FILMS, DEPTH, TOP CD AND BOTTOM CD



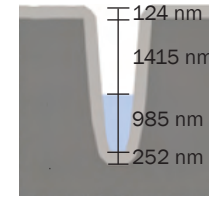
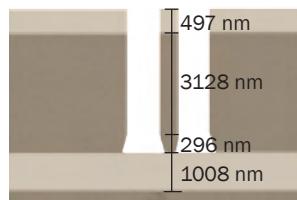
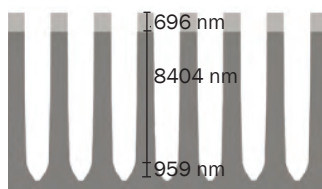
OCD Results:		Thickness Results:	
Trench Depth = 1416 Å	SiO ₂ = 252 Å	SiOC (3) = 632 Å	
Top CD = 79 nm	SiOC (1) = 404 Å	SiC (2) = 290 Å	
Bottom CD = 61 nm	SiOC (2) = 760 Å	SiC (1) = 295 Å	

PROFILE COMPARISON WITH FIB AND X-SEM

Cross Section



n&k Results



SiO₂ on Si Trench

SOI Trench (Flared CD Bottom)

Poly Recess Trench